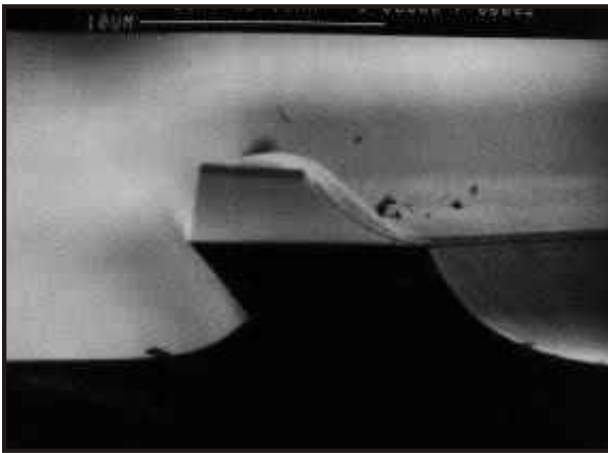


# *Ionfab Data*

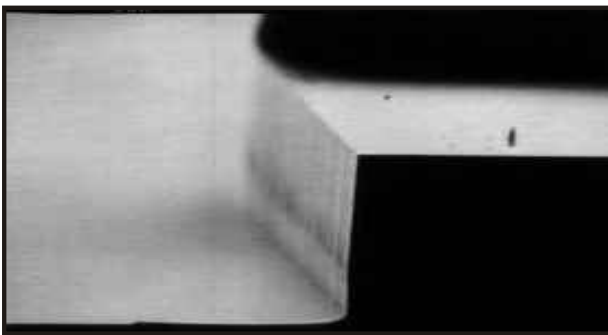
## *GaAs/AlGaAs - CAIBE Cleaved Laser Facets*



ca. 5  $\mu\text{m}$  deep etch under different angles (without substrate rotation)  
Photoresist Mask intact (not removed)

### *Ionfab 300 Plus*

Lower SEM shows a 5  $\mu\text{m}$  anisotropic etch



#### **Technology:**

Etch Mode: CAIBE

Rotating substrate with adjustable tilt

Ion Source: 15 cm, 13.56 MHz

Ion Optics: High current / Low energy

Neutralisation: filamentfree PBN

#### **Results:**

Rate: 10 - 500 nm / min

Mask: Photoresist (over SiO<sub>2</sub>)

Wall Angle: adjustable

Surface: very smooth

